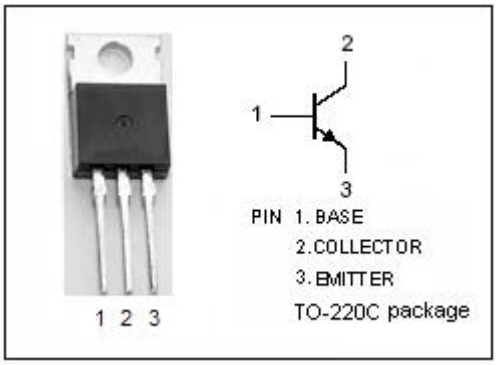
SPTECH Silicon NPN Power Transistor



DESCRIPTION

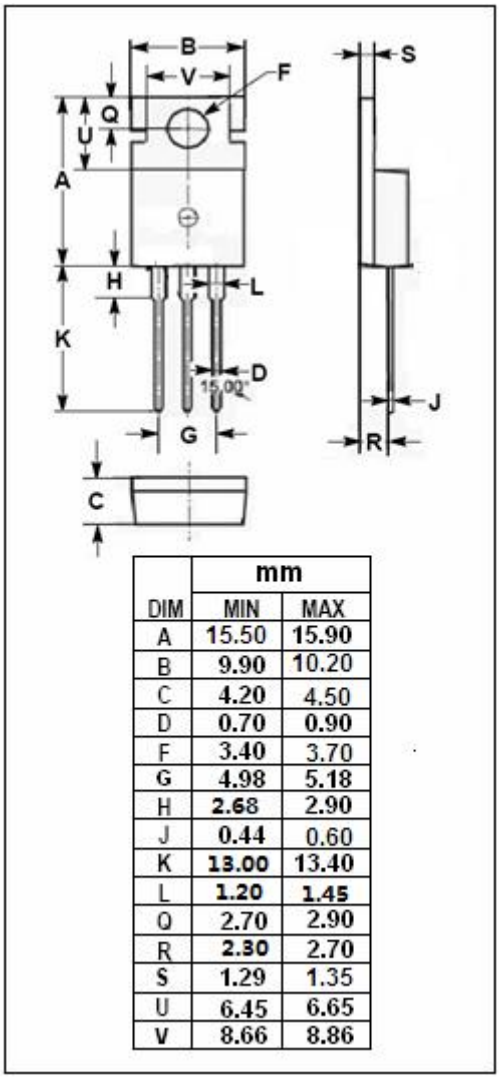
- Collector-Emitter Sustaining Voltage-
  :$V_{CEO(SUS)}$= 400V(Min)
- High Speed Switching
- Low Collector Saturation Voltage
- Wide Area of Safe Operation

APPLICATIONS

- Designed for switching regulator, DC-DC converter and ultrasonic appliance applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	2	A
I_{CM}	Collector Current-Peak	4	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

SPTECH Silicon NPN Power Transistor

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 30mA; I_B= 0	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.5A; I_B= 0.1A			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 0.5A; I_B= 0.1A			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 400V ; I_E= 0			10	μA
I_{CEX}	Collector Cutoff Current	V_{CE}= 400V;$V_{BE(off)}$=-5V V_{CE}= 400V;$V_{BE(off)}$=-5V;T_a= 125℃			10 1.0	μA mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			10	μA
h_{FE-1}	DC Current Gain	I_C= 0.1A ; V_{CE}= 5V	20		80	
h_{FE-2}	DC Current Gain	I_C= 0.5A ; V_{CE}= 5V	10			

Switching Times

t_{on}	Turn-on Time	I_C= 0.5A , R_L= 300Ω , I_{B1}= -I_{B2}= 0.1A,V_{CC}≈ 150V			1.0	μs
t_{stg}	Storage Time				2.5	μs
t_f	Fall Time				1.0	μs

◆ h_{FE-1} Classifications

M	L	K
20-40	30-60	40-80